Application No. 10/720,065

IN THE CLAIMS:

Please cancel claims 1-22, without prejudice to or disclaimer of the subject matter recited therein.

Please add claims 23-45 as follows:

LISTING OF CURRENT CLAIMS

Claims 1-22. (Canceled)

23. (New) A method to control growth of a magnetic alloy-encapsulated carbonbase nanostructure, comprising:

microwave plasma electron cyclotron resonance chemical vapor depositing an additive and a catalyst on a substrate at a power of 500W - 5000W, a working pressure of less than 5 \times 10⁻³ Torr, and under a magnetic field;

plasma pretreating said substrate by:

biasing with a direct current;

heat treating at a temperature of 400 $^{\circ}\mathrm{C}\,$ - 850 $^{\circ}\mathrm{C};$ and

etching said substrate; and

reacting said substrate with a gas and post-treating under said magnetic field.

- 24. (New) The method according to claim 23, wherein said catalyst and said additive comprise a magnetic metal or an alloy thereof.
- 25. (New) The method according to claim 23, wherein said catalyst comprises a carbon-soluble metal, an alloy thereof, or a nonmetal.
- 26. (New) The method according to claim 23, wherein said catalyst comprises

Application No. 10/720,065

a permanent magnetic rare earth element alloy having carbon solubility.

- 27. (New) The method according to claim 23, wherein said catalyst comprises a lanthanide or an alloy thereof.
- 28. (New) The method according to claim 23, wherein said additive comprises copper, gold, platinum or a lanthanide.
- 29. (New) The method according to claim 25, wherein said additive comprises copper, gold, nitrogen, chromium, boron, titanium, vanadium, zirconium, yttrium or a lanthanide.
- 30. (New) The method according to claim 23, wherein plasma pretreating changes the size, shape and activity of said catalyst.
- 31. (New) The method according to claim 23, wherein plasma pretreating controls the size, shape, and directional growth of said carbon-base nanostructure.
- 32. (New) The method according to claim 23, wherein said substrate comprises a silicon wafer, a stainless steel or a quartz glass.
- 33. (New) The method according to claim 23, wherein plasma pretreating further comprises physical vapor depositing, chemical vapor depositing, electrochemically plating, coating, or transfer printing.

Application No. 10/720,065

- 34. (New) The method according to claim 33, wherein said physical vapor depositing comprises sputtering or evaporating.
- 35. (New) The method according to claim 33, wherein said chemical vapor depositing comprises plasma enhanced chemical vapor depositing.
- 36. (New) The method according to claim 33, wherein said electrochemically plating comprises electroplating or electroless plating.
- 37. (New) The method according to claim 33, wherein said coating said substrate with a metal salt or an alloy thereof of said catalyst comprises rotating coating or immersion plating, then heating said catalyst, and reducing with hydrogen.
- 38. (New) The method according to claim 33, wherein said transfer printing with a metal salt or an alloy thereof of said catalyst comprises forming a rubber elastomer on said substrate, then heating said catalyst, and reducing with hydrogen.
- 39. (New) The method according to claim 33, wherein said substrate comprises a catalyst metal thin layer or grain layer at a surface by a photo engraving process, an electron beam lithography, a printing, a transfer printing, or an ion implantation.
- 40. (New) The method according to claim 23, wherein said substrate comprises a uniform thin layer pattern or a grain layer pattern.

- 41. (New) The method according to claim 23, wherein said substrate comprises a non-uniform thin layer pattern or grain layer pattern.
- 42. (New) The method according to claim 23, wherein said gas comprises a carbon-containing gas or a nitrogen-containing gas.
- 43. (New) The method according to claim 42, wherein said carbon-containing gas comprises methane, ethane, propane, acetylene, benzene or a mixture thereof.
- 44. (New) The method according to claim 42, wherein said nitrogen-containing gas comprises ammonia, nitrogen, an amine of methane, ethane, propane, acetylene, or benzene, or a mixture thereof.
- 45. (New) The method according to claim 23, wherein said catalyst comprises iron, cobalt, nickel, an iron-platinum alloy, a cobalt-platinum alloy, silicon, Nd₂Fe₁₄B, or Sm(Co,Cu)₅.